# 60 V, 6.0 A, Low V<sub>CE(sat)</sub> NPN Transistor

ON Semiconductor's  $e^2$ PowerEdge family of low  $V_{CE(sat)}$  transistors are surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

#### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### MAXIMUM RATINGS (TA = 25°C)

Rating	Symbol	Max	Unit	
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc	
Collector-Base Voltage	V <sub>CBO</sub>	100	Vdc	
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc	
Collector Current - Continuous	Ic	6.0	Α	
Collector Current - Peak	I <sub>CM</sub>	12.0	Α	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



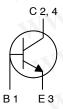
# ON Semiconductor®

http://onsemi.com

60 VOLTS, 6.0 AMPS 2.0 WATTS NPN LOW  $V_{CE(sat)}$  TRANSISTOR EQUIVALENT  $R_{DS(on)}$  50 m $\Omega$ 



SOT-223 CASE 318E STYLE 1



Schematic

#### MARKING DIAGRAM

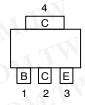


A = Assembly Location

Y = Year W = Work Week

60601 = Specific Device Code • Pb-Free Package

#### **PIN ASSIGNMENT**



Top View Pinout

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 1)	800 6.5	mW mW/°C	
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	155	°C/W	
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 2)	2 15.6	W mW/°C	
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	64	°C/W	
Total Device Dissipation (Single Pulse < 10 sec.)	P <sub>Dsingle</sub> (Note 3)	710	mW	
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSS60601MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSV60601MZ4T1G*	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSS60601MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel
NSV60601MZ4T3G*	SOT-223 (Pb-Free)	4,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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<sup>1.</sup> FR-4 @ 7.6 mm<sup>2</sup>, 1 oz. copper traces. 2. FR-4 @ 645 mm<sup>2</sup>, 1 oz. copper traces.

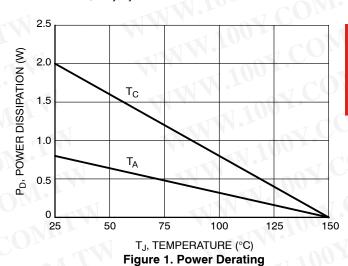
<sup>3.</sup> Thermal response.

<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			400		
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	60	-00	V.CO	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	100	11. Jan	SJ-CC	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 0.1 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	111-11		Vdc
Collector Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	_	- T- V .	0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 6.0 Vdc)	I <sub>EBO</sub>	-11	1	0.1	μAdc
ON CHARACTERISTICS				-01	7.CU
DC Current Gain (Note 4) $ \begin{array}{l} (I_C = 500 \text{ mA, V}_{CE} = 2.0 \text{ V}) \\ (I_C = 1.0 \text{ A, V}_{CE} = 2.0 \text{ V}) \\ (I_C = 2.0 \text{ A, V}_{CE} = 2.0 \text{ V}) \\ (I_C = 2.0 \text{ A, V}_{CE} = 2.0 \text{ V}) \\ (I_C = 6.0 \text{ A, V}_{CE} = 2.0 \text{ V}) \end{array} $	h <sub>FE</sub>	150 120 100 50	N-2N	360 - -	Y.C
Collector – Emitter Saturation Voltage (Note 4) ( $I_C = 0.1 \text{ A}$ , $I_B = 2.0 \text{ mA}$ ) ( $I_C = 1.0 \text{ A}$ , $I_B = 0.100 \text{ A}$ ) ( $I_C = 2.0 \text{ A}$ , $I_B = 0.200 \text{ A}$ ) ( $I_C = 3.0 \text{ A}$ , $I_B = 60 \text{ mA}$ ) ( $I_C = 6.0 \text{ A}$ , $I_B = 0.6 \text{ A}$ )	V <sub>CE(sat)</sub>	- - - -	0.045 0.085 - -	0.040 0.060 0.100 0.220 0.300	00X
Base – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 0.1 A)	V <sub>BE(sat)</sub>	_	-	0.900	V
Base – Emitter Turn–on Voltage (Note 4) $(I_C = 1.0 \text{ A, } V_{CE} = 2.0 \text{ V})$	V <sub>BE(on)</sub>	_	-	0.900	VO
Cutoff Frequency (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 10 V, f = 1.0 MHz)	of the	100	-	11-11	MHz
Input Capacitance (V <sub>EB</sub> = 5.0 V, f = 1.0 MHz)	Cibo	- 1	400		pF
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	Cobo	- 1	37	Ţ,	pF
SWITCHING CHARACTERISTICS	TO DE				
Delay (V <sub>CC</sub> = 30 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>d</sub>	-11	85	_	ns
Rise (V <sub>CC</sub> = 30 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	tr	- T	115	- < 1	ns
Storage ( $V_{CC} = 30 \text{ V}, I_{C} = 750 \text{ mA}, I_{B1} = 15 \text{ mA}$ )	t <sub>s</sub>	A T	1350	-	ns
Fall (V <sub>CC</sub> = 30 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>f</sub>	Dr.	125	-	ns

<sup>4.</sup> Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.



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## TYPICAL CHARACTERISTICS

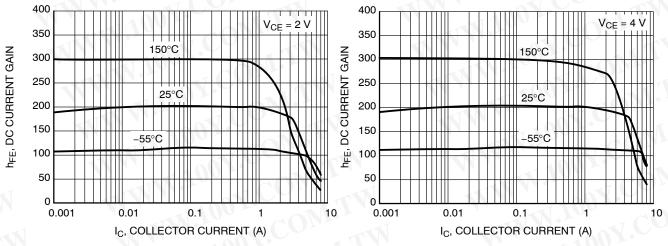


Figure 2. DC Current Gain

Figure 3. DC Current Gain

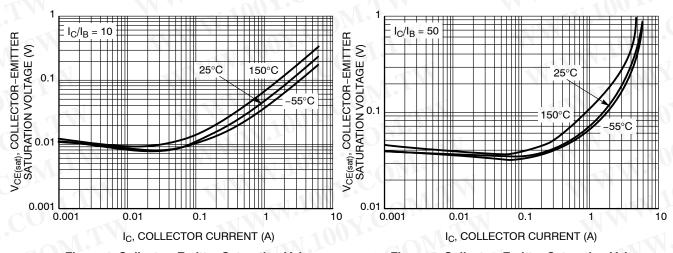


Figure 4. Collector-Emitter Saturation Voltage

Figure 5. Collector-Emitter Saturation Voltage

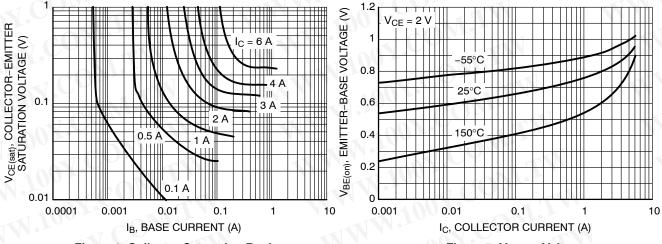
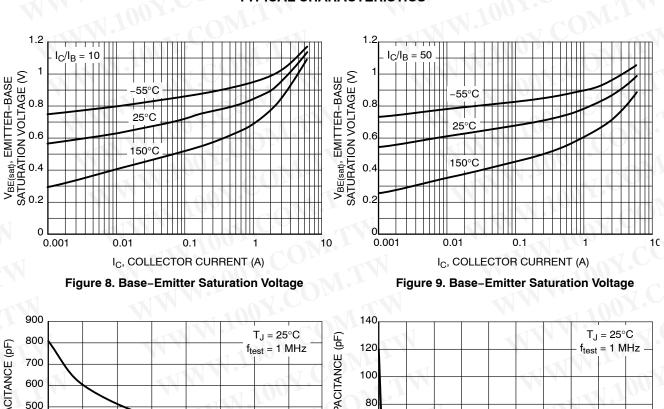


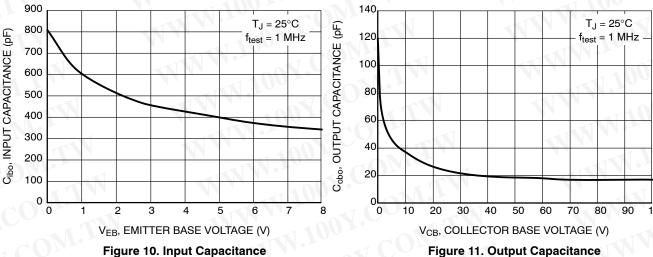
Figure 6. Collector Saturation Region

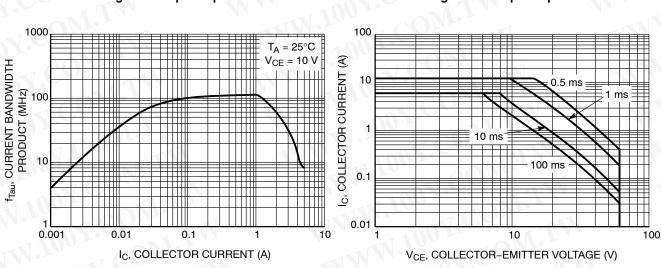
Figure 7. V<sub>BE(on)</sub> Voltage

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## TYPICAL CHARACTERISTICS

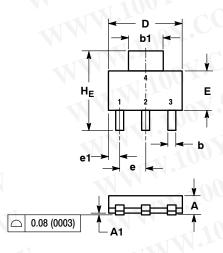


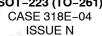




#### PACKAGE DIMENSIONS

# SOT-223 (TO-261) CASE 318E-04





- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCH.

					-	
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
O	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
Е	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
٦	0.20	727	7	0.008	O )	
L1	1.50	1.75	2.00	0.060	0.069	0.078
ΗE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	1	10°	0°	- ~	10°

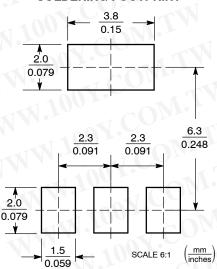
STYLE 1: PIN 1. BASE

- COLLECTOR EMITTER COLLECTOR
- 2.

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#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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